

In the Specification

Please replace the paragraph on page 1, line 1 (the title) with the following amended paragraph:

PROFILING METHOD METHOD OF DETERMINING MATERIAL USING
INTENSITY OF LIGHT

Please add the following new paragraph and heading at page 1, line 7 (before "FIELD OF THE INVENTION"):

CROSS REFERENCE TO RELATED APPLICATION

This application is a divisional of U.S. Patent Application Serial No. 09/724,813, filed November 28, 2003, entitled "Profiling Method".

Please replace the paragraph at page 16, line 20 to line 30 with the following paragraph:

Fig. 16 shows a flow chart 170 for generating the actual height profile of a reference scan of sample 160 with the measurement spot intercepting at least one point in opaque material 164 and one point in transparent material 162 and the reference spot staying in transparent material 162 in Fig. 15. In step 171 a material specific phase and thickness measurement is made of transparent material 162 preferably at the starting location of the measurement spot using, e.g., a reflectometer or ellipsometer. The thickness measurement of transparent material 162 at this location will provide the absolute thickness of the actual thickness profile and may be necessary if material 162 has more than two or three thickness values for a particular phase value. This measurement is experimentally determined because of the variation of phase with thickness. All reference points, a reference line or a reference area must be at the same thickness for a precise reference mode measurement.

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